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SEMICONDUCTOR



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## LM224DR(MS)

产品规格手册

## 概述

本电路为高性能、具有四个独立的运算放大器，内含相位补偿电路，适用于录音机和音调系统作音调均衡网络，也用于其他场合。采用 14 引线双列贴片式塑料封装 SOP-14，功耗 600mW。

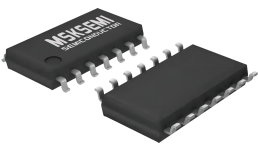
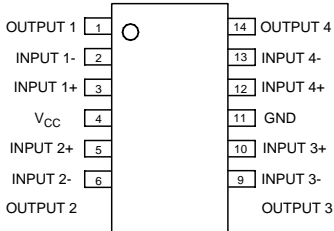

## 产品特点

- 无需外接相位补偿电路
- 电源电压范围宽：单电源时， $V_{CC}=3\sim 32V$ ，双电源时， $V_{CC}=\pm 1.5V\sim 16V$
- 功耗电流小： $I_{CC}=0.6mA$ （典型）（ $R_L=\infty$ ）
- 输入电压范围可接近地电平

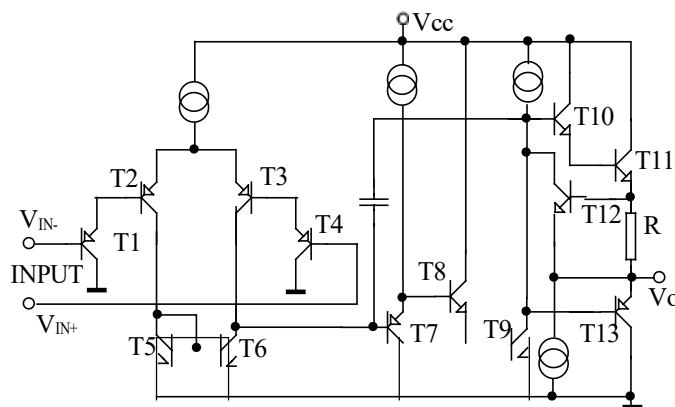
## 原理简介

LM224DR(MS) 由四个完全相同的运算放大器组成，单元电路如图所示，其工作原理简要说明如下：输入信号加到 T1、T4 基极，经差分放大后；T8、T9 于复合放大构成中间级；输出级由 T10~T13 组成。其中 T12 为保护管，当输出电流过大时，R 上压降增大使 T12 饱和导通，T12 集电极电位下降，接近  $1/2V_{CC}$ ，使得推挽管 T10、T11 和 T13 截止，从而起到保护作用。电容 C 为相位补偿电容。

## 封装形式和管脚功能定义

封装图	脚位信息	丝印
		
SOP-14		

## 内部线路图



**引脚端功能符号**

引出端序号	功 能	符 号	引出端序号	功 能	符 号
1	输出 1	OUT1	8	输出 3	OUT3
2	反向输入 1	IN- (1)	9	反向输入 3	IN- (3)
3	正向输入 1	IN+ (1)	10	正向输入 3	IN+ (3)
4	电源	Vcc	11	地	GND
5	正向输入 2	IN+ (2)	12	正向输入 4	IN+ (4)
6	反向输入 2	IN- (2)	13	反向输入 4	IN- (4)
7	输出 2	OUT2	14	输出 4	OUT4

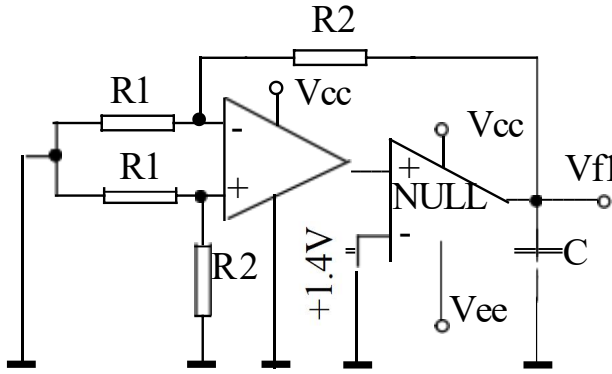
**极限参数** (绝对最大额定值, 若无其它规定,  $T_{amb}=25^{\circ}C$ )

参 数	符 号	测 试 条 件	额 定 值	单 位
电源电压	Vcc		32	V
差动输入电压	V <sub>ID</sub>		32	V
最大输入电压	V <sub>IN</sub>		-0.3~24	V
允许功耗	P <sub>D</sub>		600	mW
工作温度	T <sub>opr</sub>		0~+70	°C
贮存温度	T <sub>stg</sub>		-55~+125	°C

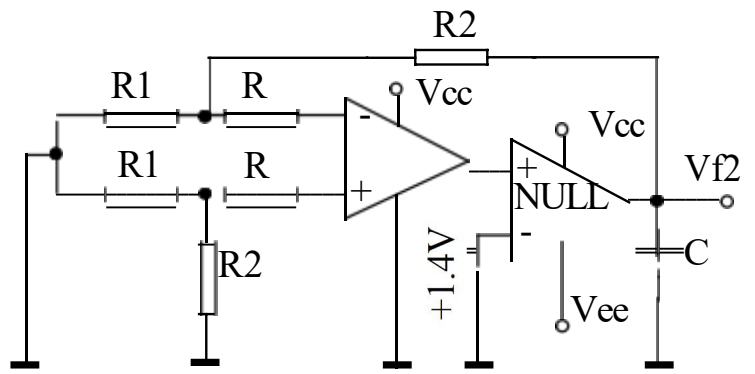
**电特性** (若无其它规定,  $V_{cc}=5V, T_{amb}=25^{\circ}C$ )

参 数	符 号	测 试 条 件	最 小 值	典 型 值	最 大 值	单 位
失调输入电压	V <sub>IO</sub>			±2	±7	mV
输入失调电流	I <sub>IO</sub>	I <sub>in(+)</sub> /I <sub>in(-)</sub>		±5	±50	nA
输入偏置电流	I <sub>BA</sub>			45	250	nA
共模输入电压范围	V <sub>ICM</sub>		0		V <sub>cc</sub> -1.5	V
共模抑制比	K <sub>CMR</sub>		56			dB
强信号电压增益	G <sub>v</sub>	V <sub>cc</sub> =15V, R <sub>L</sub> ≥ 2 kΩ	25	100		V/mV
输出电压范围	V <sub>O</sub>		0		V <sub>cc</sub> -1.5	V
电源纹波抑制比	PSRR		65			dB
通 道 分 离	C <sub>s</sub>	f=1kHz~20kHz		120		dB
静态消耗电流 (1)	I <sub>cc</sub>			0.6	2	mA
静态消耗电流 (2)	I <sub>cc</sub>	V <sub>cc</sub> =20V		1.5	3	mA
输出拉电流	I <sub>o</sub>	V <sub>in+</sub> =1V, V <sub>in-</sub> =0V	20	40		mA
输出灌电流	I <sub>o</sub>	V <sub>in+</sub> =0V, V <sub>in-</sub> =1V	10	20		mA

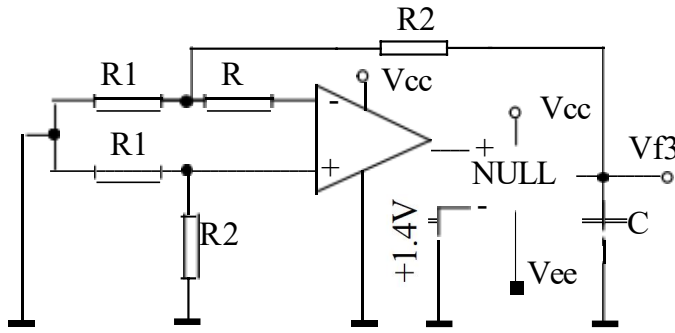
**测试原理图** (注: NULL 指零放大器)



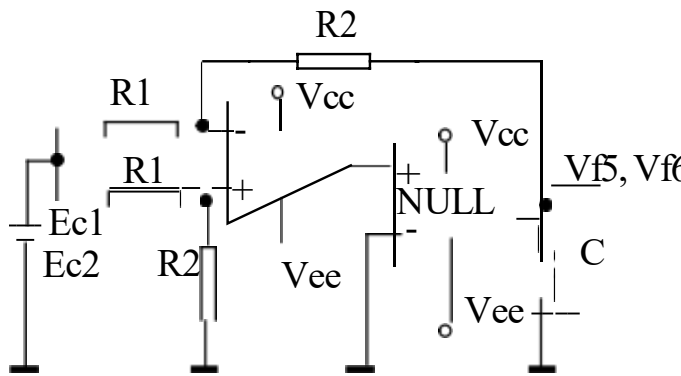
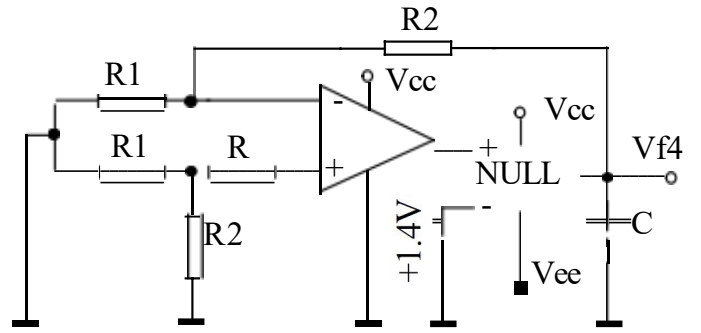
$V_{io} = V_{f1} / (1 + R2/R1)$   
输入失调电压  $V_{io}$  测试图



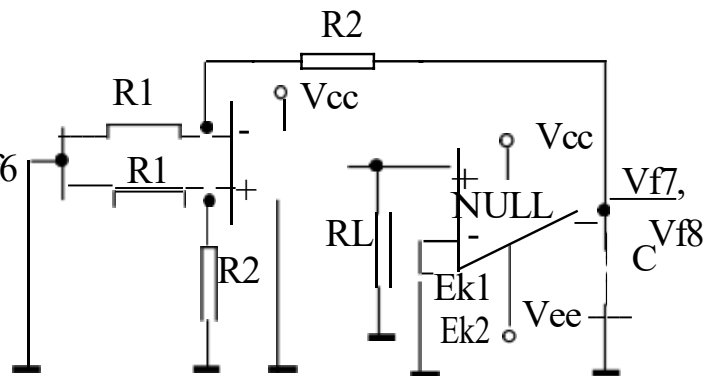
$I_{io} = (V_{f2} - V_{f1}) / R (1 + R2/R1)$   
输入失调电流  $I_{io}$  测试图



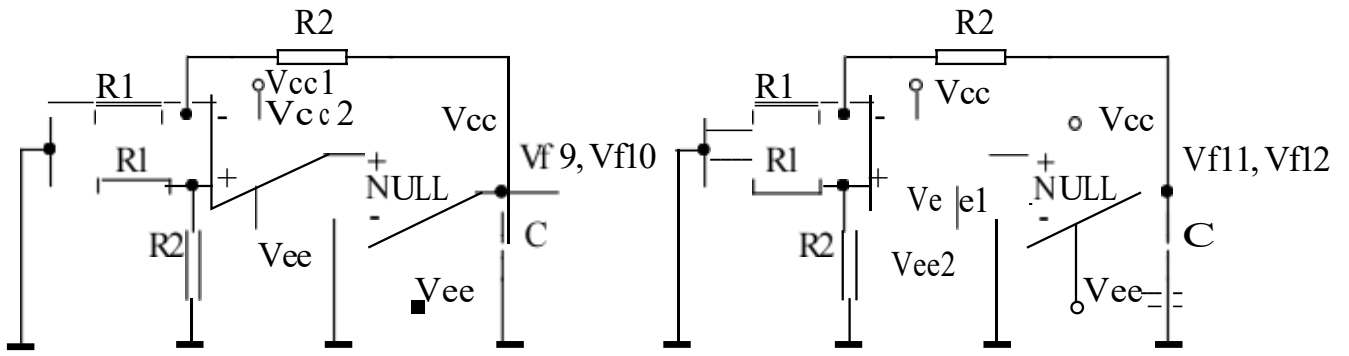
$I_{BA} = (V_{f4} - V_{f3}) / 2R (1 + R2/R1)$   
输入偏置电流  $I_{BA}$  测试图



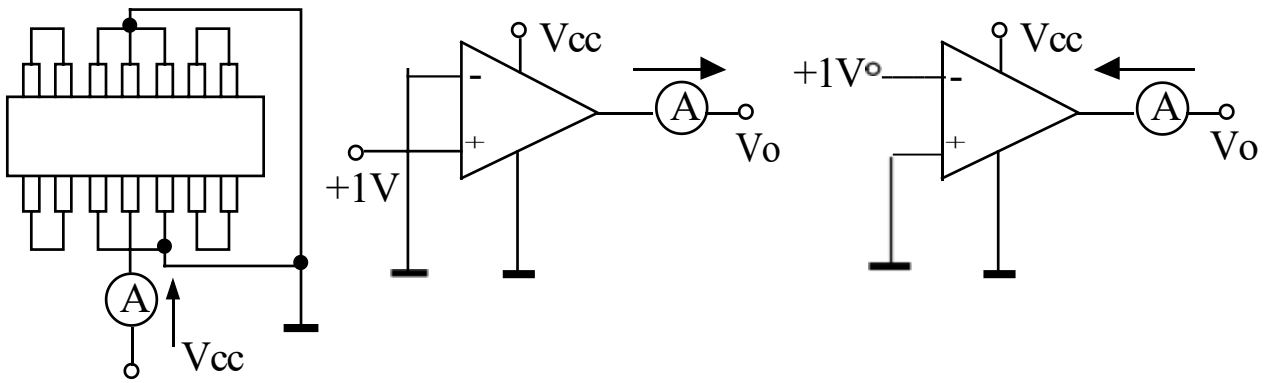
$CMR = 20 \log (E_{c1} - E_{c2}) (1 + R2/R1) / (V_{f5} - V_{f6})$   
共模抑制比  $CMR$  及共模输入电压范围  $V_{ICM}$  测试图



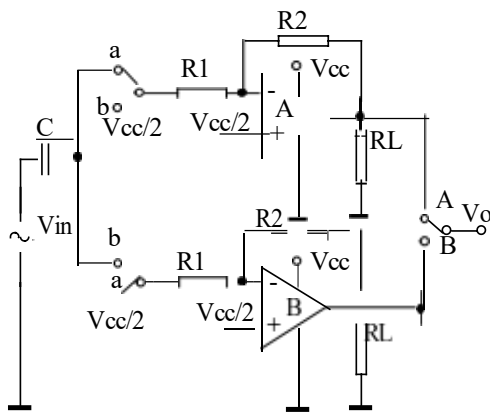
$G_v = (E_{k1} - E_{k2}) (1 + R2/R1) / (V_{f8} - V_{f7})$   
电压增益  $G_v$  测试图



$PSRR (+) = 20 \log \frac{(V_{cc1} - V_{cc2}) (1 + R2/R1)}{(V_{f9} - V_{f10})}$      
  $PSRR (-) = 20 \log \frac{(V_{ee1} - V_{ee2}) (1 + R2/R1)}{(V_{f11} - V_{f12})}$   
 电源纹波抑制比 PSRR 测试图



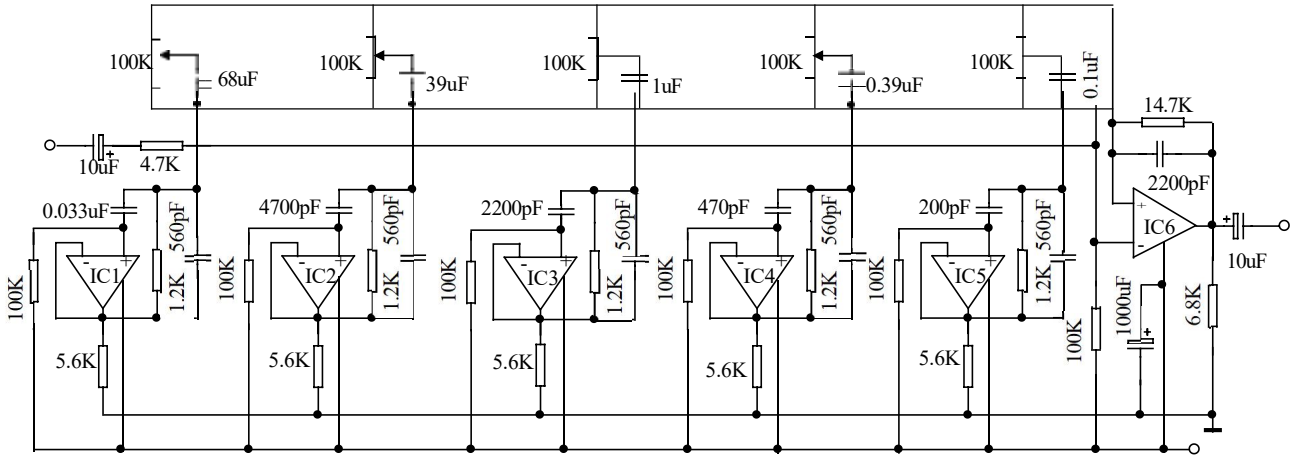
消耗电流  $I_{cc}$  及输出电流  $I_o$  测试图



通道分离度  $C_s$  测试图

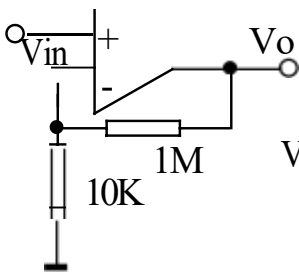
SW: A  
 $C_s (A) = 20 \log \frac{R2 * V_{OA}}{R1 * V_{OB}}$   
 SW: B  
 $C_s (B) = 20 \log \frac{R2 * V_{OB}}{R1 * V_{OA}}$

**应用图**

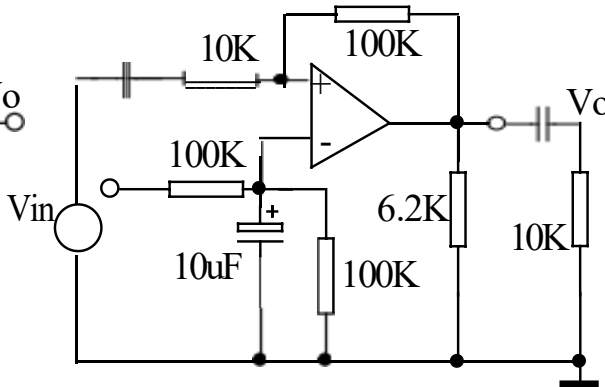


LM224用于五频率音调控制电路

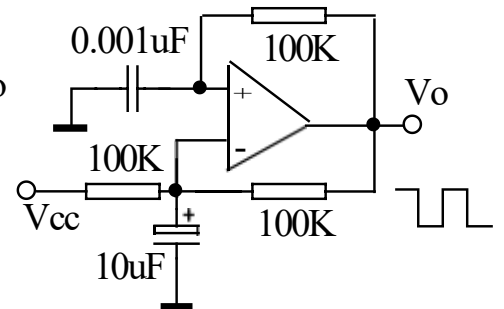
直流放大器



倒相放大器

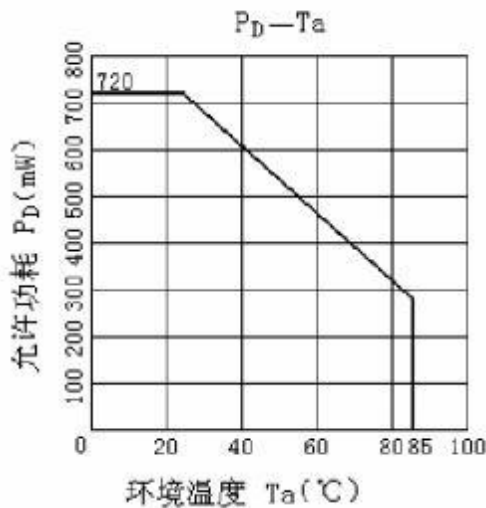


矩形波发生器

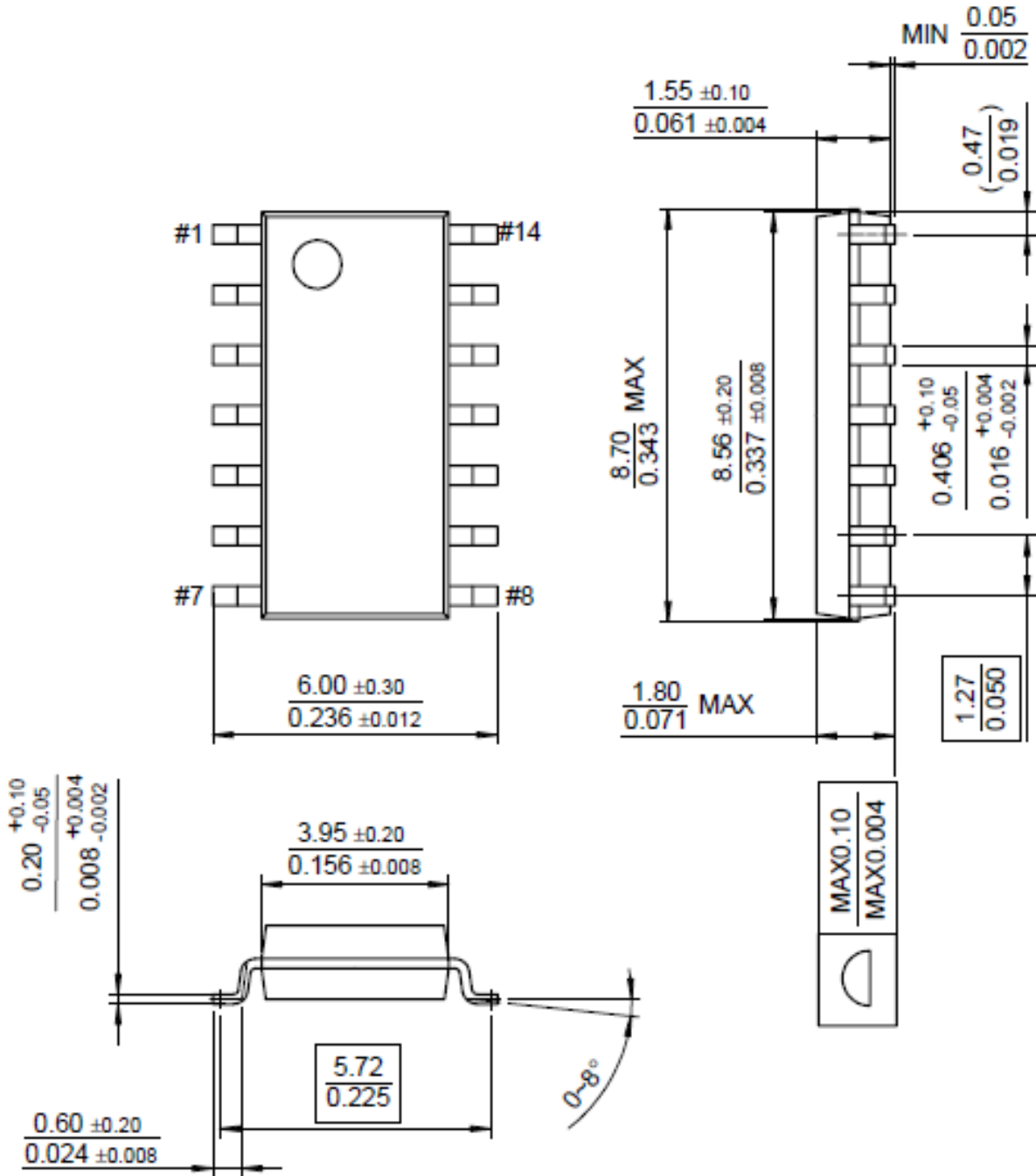


LM224的其它应用

**特性曲线**



SOP14



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P/N	PKG	QTY
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